

SILICON NPN TRANSISTOR EPITAXIAL PLANAR TYPE (PCT PROCESS)

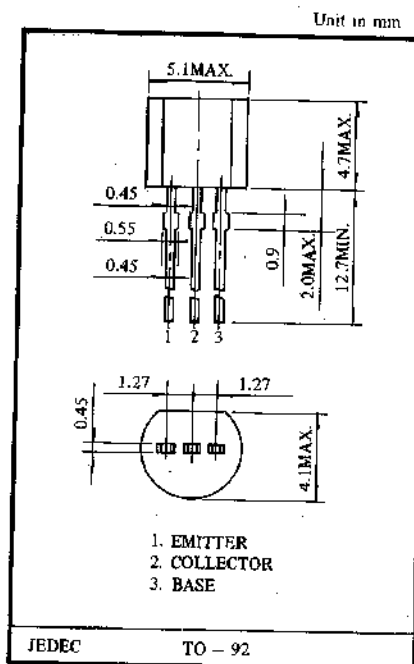
2SC3203

APPLICATIONS

- Low Frequency Power Amplifiers
(B-Class Push-pull, $P_o=1W$)
- General Purpose Switching Circuits

FEATURES

- Excellent h_{FE} vs. Collector Current Characteristics
- $P_c=600mW$, $I_c=800mA$ max.
- $V_{CE(sat)}=0.5V$ max at $I_c=500mA$, $I_b=20mA$
- Complementary to the 2SA1271



■ MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	35	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current	I_c	800	mA

CHARACTERISTIC	SYMBOL	RATING	UNIT
Emitter Current	I_E	-800	mA
Collector Power Dissipation	P_c	600	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut off Current	I_{CBO}	$V_{CB}=35V$, $I_E=0$	-	-	100	nA
Emitter Cut off Current	I_{EBO}	$V_{EB}=5V$, $I_c=0$	-	-	100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_c=10mA$	30	-	-	V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=1V$, $I_c=100mA$	100	-	320	
	$h_{FE(2)}$	$V_{CE}=1V$, $I_c=700mA$	35	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c=500mA$, $I_b=20mA$	-	-	0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=1V$, $I_c=10mA$	0.5	-	0.8	V
Transition Frequency	f_T	$V_{CE}=5V$, $I_c=10mA$	-	120	-	MHz
Output Capacitance	C_{ob}	$V_{CB}=10V$, $f=1MHz$	-	13	-	pF

NOTE: According to h_{FE} (1), Classified as follows

0	100-200	Y	160-320
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